

ABSTRACT OF THE DISCLOSURE

A method for manufacturing a semiconductor device having flat pads. An opening and island-like dielectric films are first formed in a dielectric film. The opening is then filled with metal, and a metal layer is formed on the dielectric film. The upper surface of the metal layer is flattened using the CMP technique with the upper surface of the dielectric film functioning as a stopper. The island-like dielectric films prevent the occurrence of dishing in a conductive portion.

10076355-021902